

AMENDMENTS TO THE CLAIMS

The status of the claims of the present application stands as follows:

1. (Canceled).
2. (Currently amended) ~~An exhaust gas scrubber~~ A system according to claim 26 27, wherein said at least one substrate is made of quartz.
3. (Currently amended) ~~An exhaust gas scrubber~~ A system according to claim 26 27, wherein said at least one substrate forms a baffle within said second chamber.
4. (Currently amended) ~~An exhaust gas scrubber~~ A system according to claim 3, wherein said baffle includes a plurality of apertures for allowing ~~the said~~ exhaust gas to flow through said baffle.
5. (Currently amended) ~~An exhaust gas scrubber~~ A system according to claim 26 27, further comprising a plurality of said substrates forming a series of baffles within said second chamber.
6. (Currently amended) ~~An exhaust gas scrubber~~ A system according to claim 5, wherein each baffle of said series of baffles includes a plurality of apertures for allowing the said exhaust gas to flow through each of said series of baffles.
7. (Currently amended) ~~An exhaust gas scrubber~~ A system according to claim 5, wherein said series of baffles define a serpentine passageway within said second chamber.
8. (Currently amended) ~~An exhaust gas scrubber~~ A system according to claim 26 27, further comprising a heating element for heating at least one of said second chamber and said at least one substrate.

9. (Currently amended) ~~An exhaust gas scrubber~~ A system according to claim 26 27, wherein said at least one substrate is removable and reusable ~~after the film has been removed.~~
10. (Currently amended) ~~An exhaust gas scrubber~~ A system according to claim 26 27, wherein ~~the at least one chemical~~ said second component of ~~the said exhaust gas~~ is comprises silicon.
11. (Withdrawn) A system according to claim 10, further comprising a pump located between said first chamber and said second chamber for pumping the gas from said first chamber to said second chamber via said gas inlet.
12. (Withdrawn) A system according to claim 10, further comprising a heating element for heating at least one of the gas and said at least one substrate.
13. (Withdrawn) A system according to claim 10, further comprising an abatement device for removing at least one component of the exhaust gas not deposited on said substrate.
14. (Withdrawn) A scrubber for scrubbing a gas containing a non-toxic part and a toxic part, the scrubber comprising:
- a. a first enclosure defining a first chamber for receiving the gas, said first chamber for removing at least a portion of the non-toxic part of the exhaust gas by chemical vapor deposition; and
 - b. a second enclosure defining a second chamber in fluid communication with said first chamber, said second chamber for receiving at least a portion of the gas, said second chamber for removing at least a portion of the toxic part from the gas.
15. (Currently amended) A scrubber system ~~for scrubbing a gas containing a non-toxic part and a toxic part, the scrubber~~, comprising:
- a. a processing chamber operatively configured to contain a process;
 - b. an exhaust gas generated by said process and consisting of a non-toxic part and a toxic part;

- c. a first apparatus, in fluid communication with said processing chamber, ~~and adapted for removing at least a portion of the said non-toxic part of the said exhaust gas by chemical vapor deposition; and~~
- d. ~~a second apparatus, in fluid communication with said processing chamber~~ first apparatus, ~~and adapted for removing at least a portion of the said toxic part from the said exhaust gas.~~
16. (Currently amended) A scrubber system according to claim 15, further comprising a substrate located in within said first ~~enclosure~~ apparatus, said substrate ~~for~~ receiving by chemical vapor deposition a film containing the said non-toxic part of the said exhaust gas.
17. (Currently amended) A scrubber system according to claim 15, wherein ~~the said~~ non-toxic part comprises silicon.
18. (Currently amended) A scrubber system according to claim 15, wherein ~~the said~~ toxic part comprises arsenic.
19. (Withdrawn) A method for scrubbing an exhaust gas of a manufacturing process, the exhaust gas comprising a first chemical component and a second chemical component, comprising the steps of:
- flowing the exhaust gas through an enclosure defining a chamber and containing at least one substrate; and
 - causing the first chemical component to be chemical vapor deposited onto said at least one substrate.
20. (Withdrawn) A method according to claim 19, further comprising the step of removing the second chemical component from the exhaust gas after performing step b).
21. (Withdrawn) A method according to claim 19, wherein step b) is performed by heating at least one of said at least one substrate and said enclosure to at least 800°C.

22. **(Withdrawn)** A method according to claim 21, wherein step b) is performed by heating at least one of said at least one substrate and said enclosure to at least 1100°C.
23. **(Withdrawn)** A method according to claim 19, wherein the first chemical component is non-toxic and the second chemical component is non-toxic.
24. **(Withdrawn)** A method according to claim 23, wherein the first chemical component comprises silicon and the second chemical component comprises arsenic.
25. **(Withdrawn)** A method according to claim 19, further comprising after step b) the steps of:
- removing said at least one substrate from said enclosure;
 - cleaning said at least one substrate of any film deposited thereon;
 - installing said at least one substrate in said enclosure;
 - again causing the first chemical component to be chemical vapor deposited onto said at least one substrate.
26. **(Canceled)**
27. **(New)** A system, comprising:
- a first chamber operatively configured to contain a process;
 - an exhaust gas resulting from said process and consisting of a first component and a second component; and
 - a second chamber that includes an inlet and an outlet and contains at least one substrate, said inlet receiving said exhaust gas, said outlet exhausting from said second chamber substantially only said first component of said exhaust gas, and said at least one substrate having deposited thereon by vapor deposition said second component of said exhaust gas.

[THE REST OF THIS PAGE INTENTIONALLY LEFT BLANK]

BTX.266795.1